

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

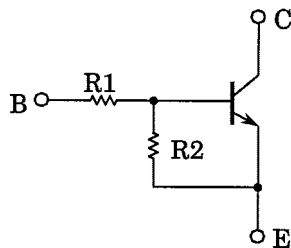
RN1107F, RN1108F, RN1109F

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

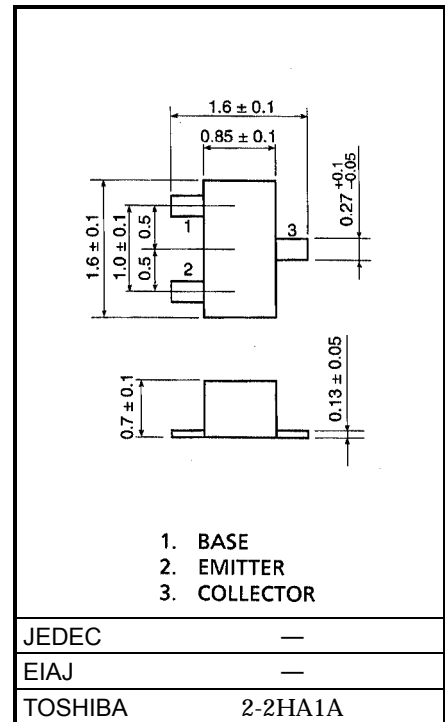
Unit in mm

- With built-in bias resistors.
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2107F~2109F

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN1107F	10	47
RN1108F	22	47
RN1109F	47	22



Maximum Ratings (Ta = 25°C)

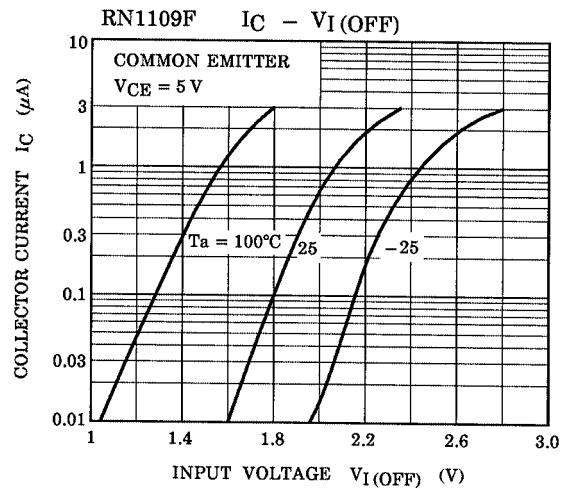
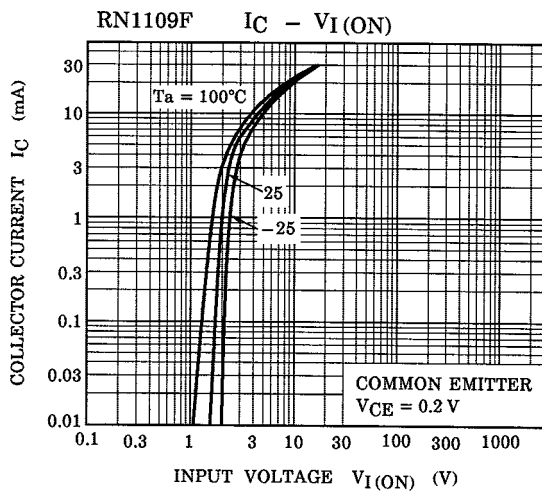
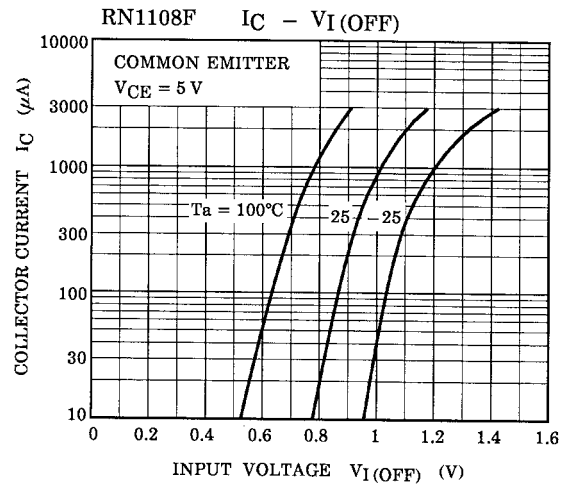
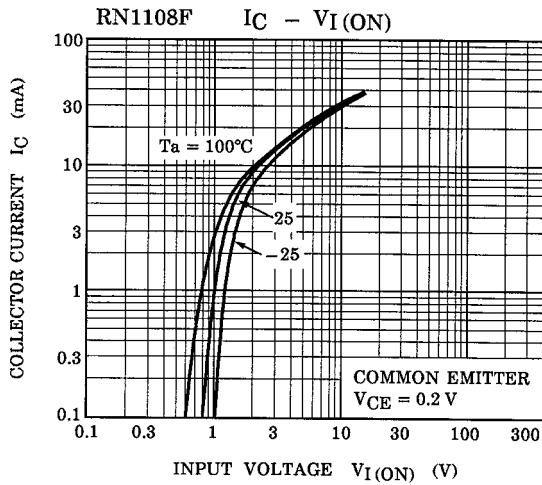
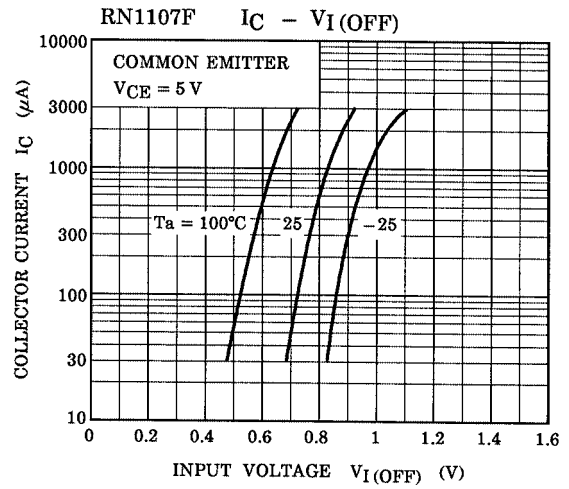
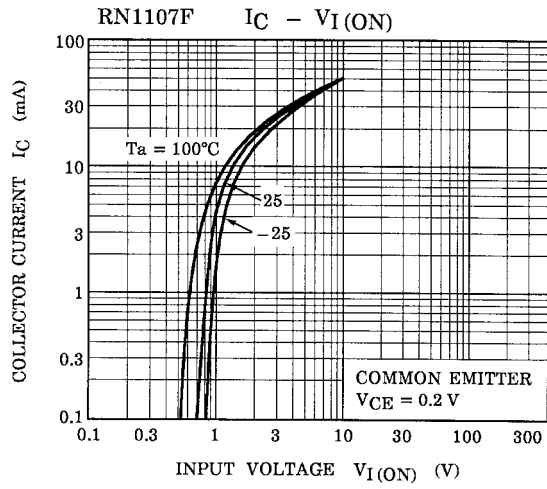
Characteristic	Symbol	Rating	Unit	
Collector-base voltage	RN1107F~1109F	V _{CBO}	50	V
Collector-emitter voltage	RN1107F~1109F	V _{CEO}	50	V
Emitter-base voltage	RN1107F	V _{EBO}	6	V
	RN1108F		7	
	RN1109F		15	
Collector current	RN1107F~1109F	I _c	100	mA
Collector power dissipation	RN1107F~1109F	P _c	100	mW
Junction temperature	RN1107F~1109F	T _j	150	°C
Storage temperature range	RN1107F~1109F	T _{stg}	-55~150	°C

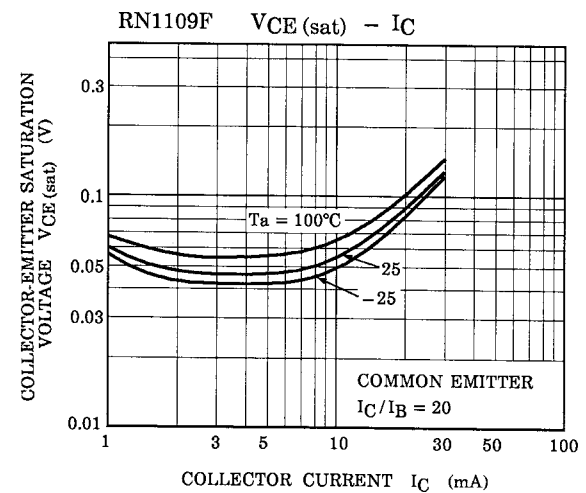
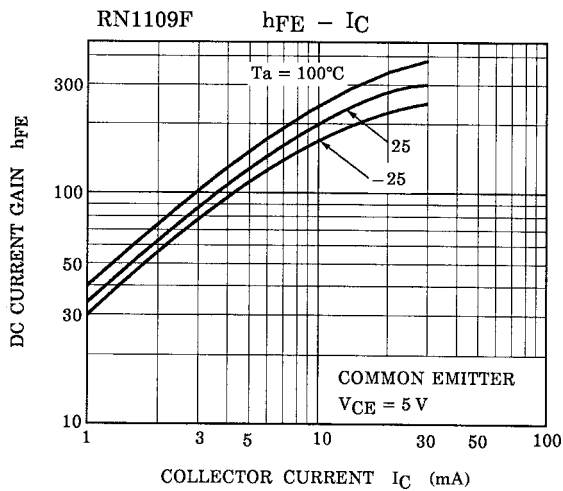
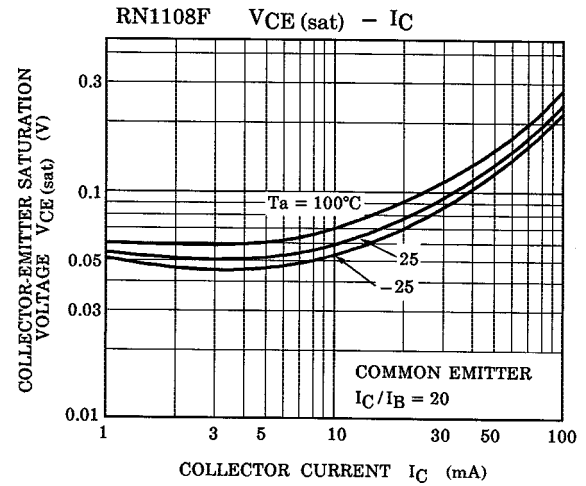
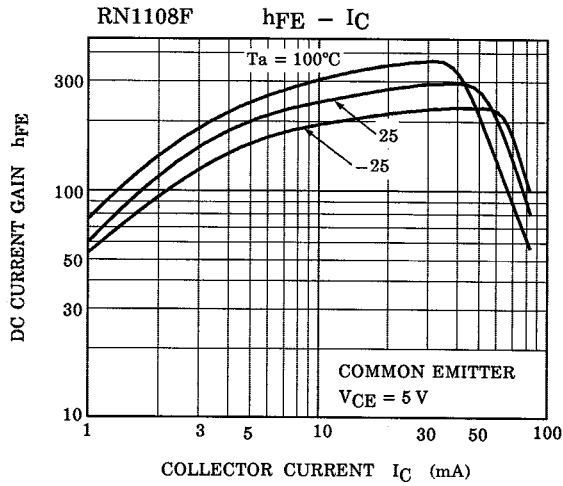
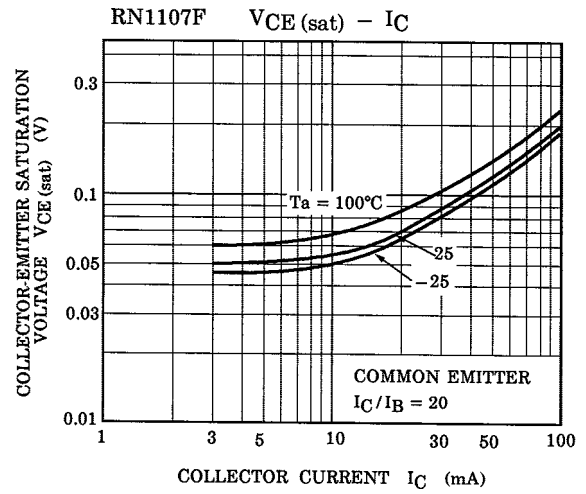
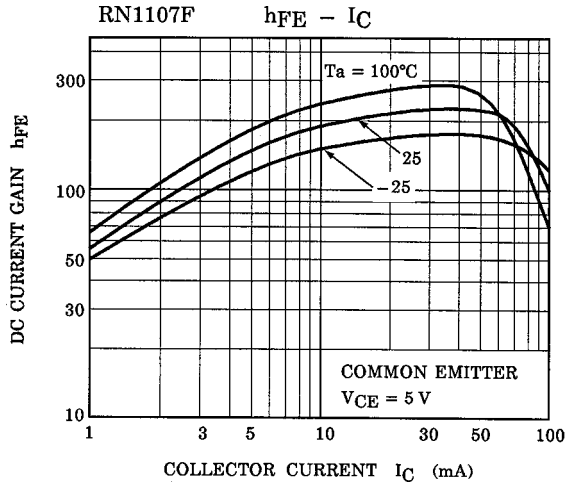
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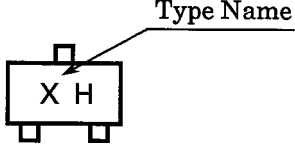
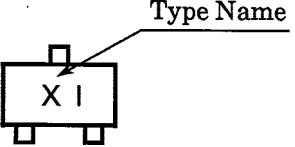
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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN1107F~1109F	I_{CBO}	—	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
		I_{CEO}	—	$V_{CE} = 50V, I_B = 0$	—	—	500	nA
Emitter cut-off current	RN1107F	I_{EBO}	—	$V_{EB} = 6V, I_C = 0$	0.081	—	0.15	mA
	RN1108F		—	$V_{EB} = 7V, I_C = 0$	0.078	—	0.145	
	RN1109F		—	$V_{EB} = 15V, I_C = 0$	0.167	—	0.311	
DC current gain	RN1107F	h_{FE}	—	$V_{CE} = 5V, I_C = 10mA$	80	—	—	—
	RN1108F		—		80	—	—	
	RN1109F		—		70	—	—	
Collector-emitter saturation voltage	RN1107F~1109F	$V_{CE(sat)}$	—	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Input voltage (ON)	RN1107F	$V_{I(ON)}$	—	$V_{CE} = 0.2V, I_C = 5mA$	0.7	—	1.8	V
	RN1108F		—		1.0	—	2.6	
	RN1109F		—		2.2	—	5.8	
Input voltage (OFF)	RN1107F	$V_{I(OFF)}$	—	$V_{CE} = 5V, I_C = 0.1mA$	0.5	—	1.0	V
	RN1108F		—		0.6	—	1.16	
	RN1109F		—		1.5	—	2.6	
Translation frequency	RN1107F~1109F	f_T	—	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector output capacitance	RN1107F~1109F	C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input Resistor	RN1107F	R1	—	—	7	10	13	kΩ
	RN1108F		—		15.4	22	28.6	
	RN1109F		—		32.9	47	61.1	
Resistor Ratio	RN1107F	R1/R2	—	—	0.191	0.213	0.232	—
	RN1108F		—		0.421	0.468	0.515	
	RN1109F		—		1.92	2.14	2.35	





Type Name	Marking
RN1107F	
RN1108F	
RN1109F	